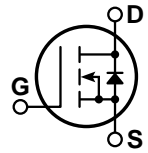
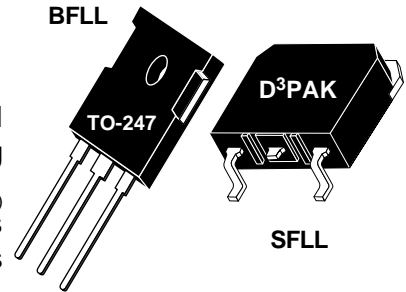


**POWER MOS 7® FREDFET**

Power MOS 7® is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETS. Both conduction and switching losses are addressed with Power MOS 7® by significantly lowering  $R_{DS(ON)}$  and  $Q_g$ . Power MOS 7® combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.

- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge,  $Q_g$
- Increased Power Dissipation
- Easier To Drive
- TO-247 or Surface Mount D<sup>3</sup>PAK Package
- **FAST RECOVERY BODY DIODE**


**MAXIMUM RATINGS**

 All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

| Symbol         | Parameter  | APT1001R6BFLL/SFLL | UNIT                |
|----------------|--|--------------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage   | 1000               | Volts               |
| $I_D$          | Continuous Drain Current @ $T_C = 25^\circ\text{C}$            | 8                  | Amps                |
| $I_{DM}$       | Pulsed Drain Current <sup>①</sup>                              | 32                 |                     |
| $V_{GS}$       | Gate-Source Voltage Continuous                                 | $\pm 30$           | Volts               |
| $V_{GSM}$      | Gate-Source Voltage Transient                                  | $\pm 40$           |                     |
| $P_D$          | Total Power Dissipation @ $T_C = 25^\circ\text{C}$             | 266                | Watts               |
|                | Linear Derating Factor   | 2.13               | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range               | -55 to 150         | $^\circ\text{C}$    |
| $T_L$          | Lead Temperature: 0.063" from Case for 10 Sec.                 | 300                |                     |
| $I_{AR}$       | Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive) | 4                  | Amps                |
| $E_{AR}$       | Repetitive Avalanche Energy <sup>①</sup>                       | 16                 | mJ                  |
| $E_{AS}$       | Single Pulse Avalanche Energy <sup>④</sup>                     | 425                |                     |

**STATIC ELECTRICAL CHARACTERISTICS**

| Symbol       | Characteristic / Test Conditions   | MIN  | TYP | MAX       | UNIT          |
|--------------|--|------|-----|-----------|---------------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )                             | 1000 |     |           | Volts         |
| $I_{D(on)}$  | On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ ) | 8    |     |           | Amps          |
| $R_{DS(on)}$ | Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10V, I_D = 4A$ )                         |      |     | 1.60      | Ohms          |
| $I_{DSS}$    | Zero Gate Voltage Drain Current ( $V_{DS} = 800V, V_{GS} = 0V$ )                                   |      |     | 250       | $\mu\text{A}$ |
|              | Zero Gate Voltage Drain Current ( $V_{DS} = 500V, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )          |      |     | 1000      |               |
| $I_{GSS}$    | Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )                                    |      |     | $\pm 100$ | nA            |
| $V_{GS(th)}$ | Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 1\text{mA}$ )                                     | 3    |     | 5         | Volts         |

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

### DYNAMIC CHARACTERISTICS

APT1001R6BFL/SFL

| Symbol       | Characteristic                 | Test Conditions   | MIN | TYP  | MAX | UNIT |
|--------------|--------------------------------|---|-----|------|-----|------|
| $C_{iss}$    | Input Capacitance              | $V_{GS} = 0V$<br>$V_{DS} = 25V$<br>$f = 1\text{ MHz}$                             |     | 1322 |     | pF   |
| $C_{oss}$    | Output Capacitance             |   |     | 230  |     |      |
| $C_{riss}$   | Reverse Transfer Capacitance   |   |     | 42   |     |      |
| $Q_g$        | Total Gate Charge <sup>③</sup> | $V_{GS} = 10V$<br>$V_{DD} = 500V$<br>$I_D = 8A @ 25^\circ C$                      |     | 53   |     | nC   |
| $Q_{gs}$     | Gate-Source Charge             |   |     | 7    |     |      |
| $Q_{gd}$     | Gate-Drain ("Miller") Charge   |   |     | 35   |     |      |
| $t_{d(on)}$  | Turn-on Delay Time             | $V_{GS} = 15V$<br>$V_{DD} = 500V$<br>$I_D = 8A @ 25^\circ C$<br>$R_G = 0.6\Omega$ |     | 18   |     | ns   |
| $t_r$        | Rise Time                      |   |     | 18   |     |      |
| $t_{d(off)}$ | Turn-off Delay Time            |   |     | 32   |     |      |
| $t_f$        | Fall Time                      |   |     | 19   |     |      |

### SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

| Symbol    | Characteristic / Test Conditions                                | MIN                 | TYP | MAX  | UNIT    |
|-----------|---|---------------------|-----|------|---------|
| $I_S$     | Continuous Source Current (Body Diode)                          |                     |     | 8    | Amps    |
| $I_{SM}$  | Pulsed Source Current <sup>①</sup> (Body Diode)                 |                     |     | 32   |         |
| $V_{SD}$  | Diode Forward Voltage <sup>②</sup> ( $V_{GS} = 0V, I_S = -8A$ ) |                     |     | 1.3  | Volts   |
| $dv/dt$   | Peak Diode Recovery $dv/dt$ <sup>⑤</sup>                        |                     |     | 18   | V/ns    |
| $t_{rr}$  | Reverse Recovery Time<br>( $I_S = -8A, di/dt = 100A/\mu s$ )    | $T_j = 25^\circ C$  |     | 250  | ns      |
|           |   | $T_j = 125^\circ C$ |     | 515  |         |
| $Q_{rr}$  | Reverse Recovery Charge<br>( $I_S = -8A, di/dt = 100A/\mu s$ )  | $T_j = 25^\circ C$  |     | 0.50 | $\mu C$ |
|           |   | $T_j = 125^\circ C$ |     | 1.1  |         |
| $I_{RRM}$ | Peak Recovery Current<br>( $I_S = -8A, di/dt = 100A/\mu s$ )    | $T_j = 25^\circ C$  |     | 8.3  | Amps    |
|           |   | $T_j = 125^\circ C$ |     | 11.5 |         |

### THERMAL CHARACTERISTICS

| Symbol          | Characteristic      | MIN | TYP | MAX  | UNIT         |
|-----------------|---------------------|-----|-----|------|--------------|
| $R_{\theta JC}$ | Junction to Case    |     |     | 0.47 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction to Ambient |     |     | 40   |              |

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380  $\mu s$ , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting  $T_j = +25^\circ C$ ,  $L = 13.28mH$ ,  $R_G = 25\Omega$ , Peak  $I_L = 8A$

⑤  $dv/dt$  numbers reflect the limitations of the test circuit rather than the device itself.  $I_S \leq -8A$   $di/dt \leq 700A/\mu s$   $V_R \leq V_{DSS}$   $T_j \leq 150^\circ C$

APT Reserves the right to change, without notice, the specifications and information contained herein.

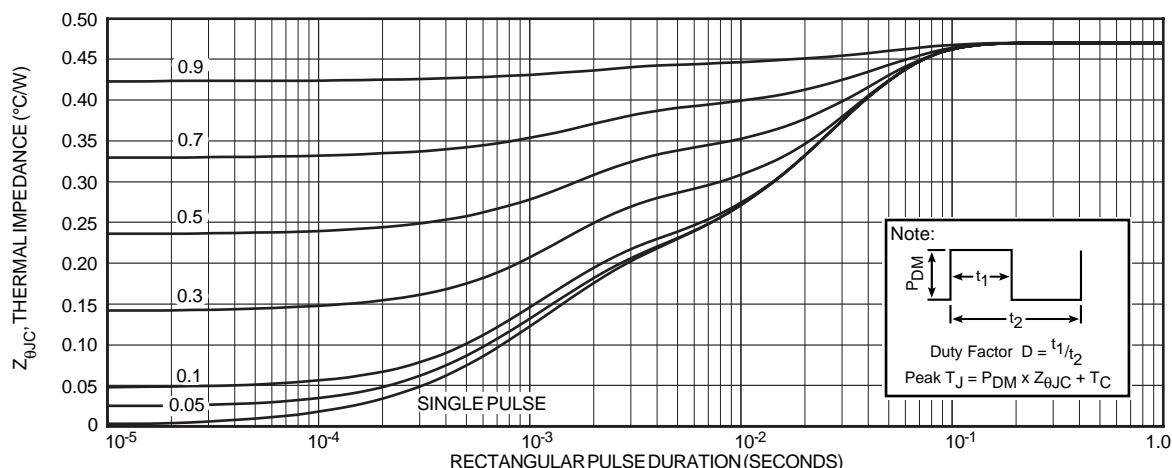


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

# Typical Performance Curves

APT1001R6BFLL/SFLL

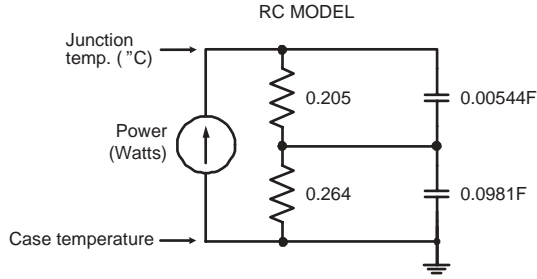


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

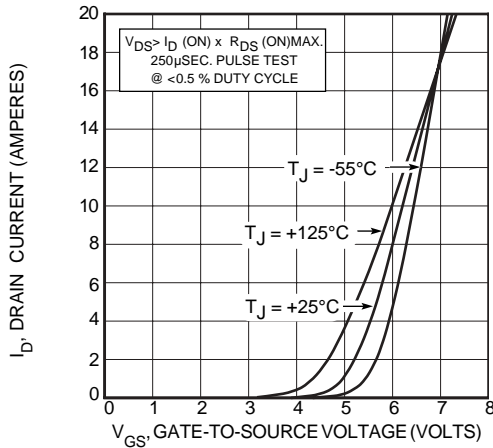


FIGURE 4, TRANSFER CHARACTERISTICS

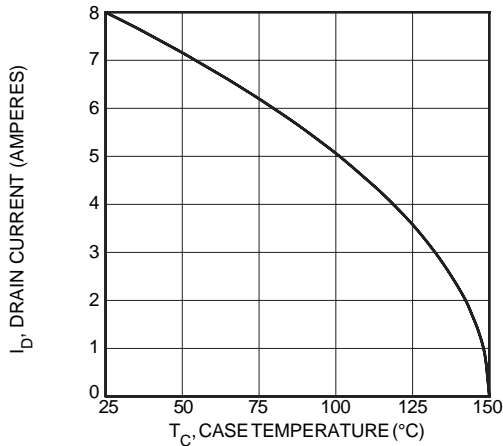


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

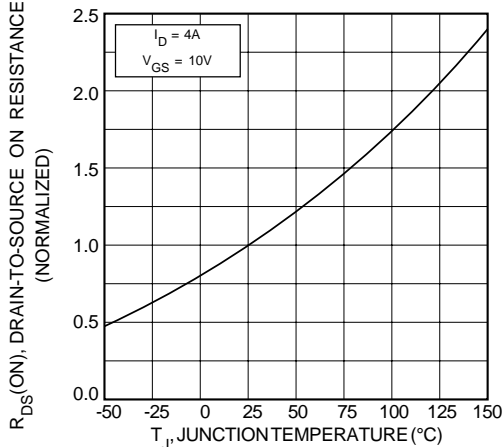


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

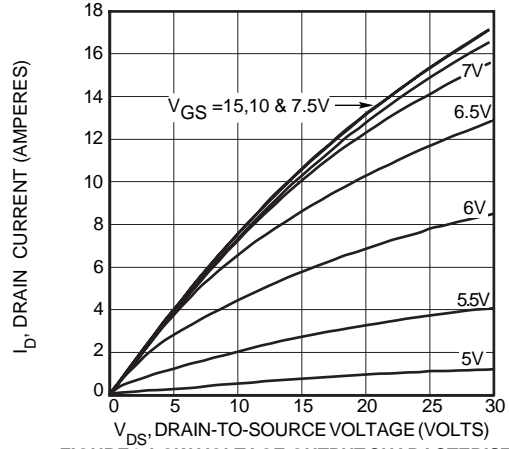


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

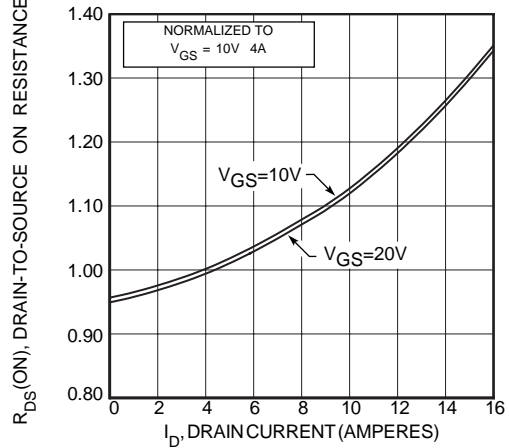


FIGURE 5, RDS(ON) vs DRAIN CURRENT

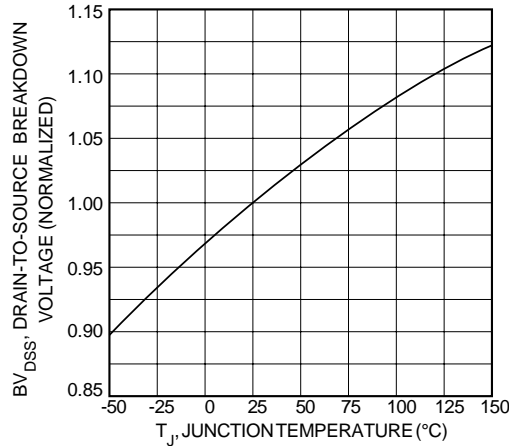


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

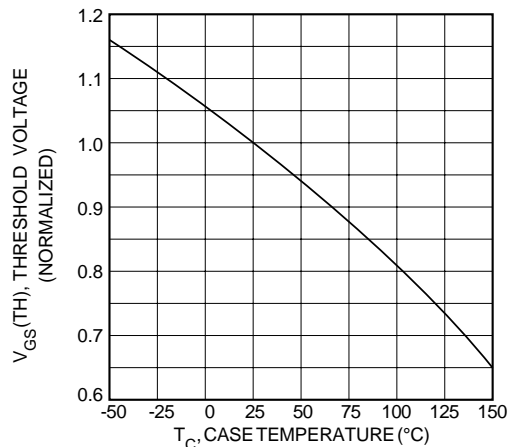


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

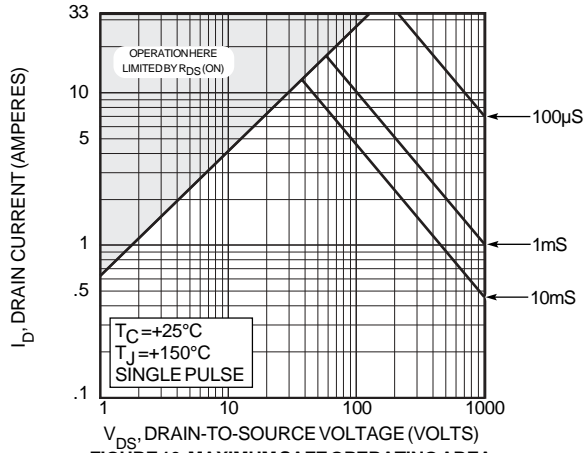


FIGURE 10, MAXIMUM SAFE OPERATING AREA

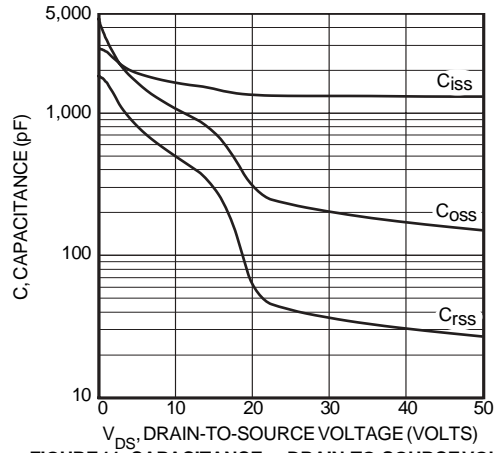


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

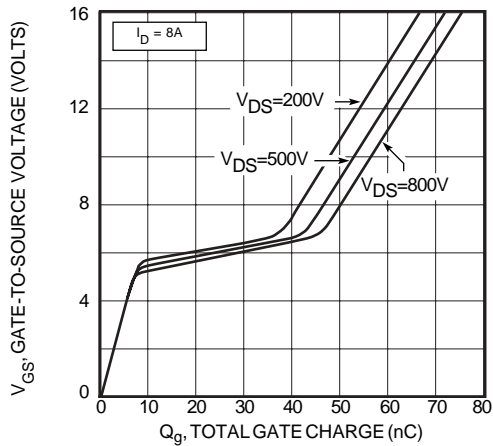


FIGURE 12, GATE CHARGE vs GATE-TO-SOURCE VOLTAGE

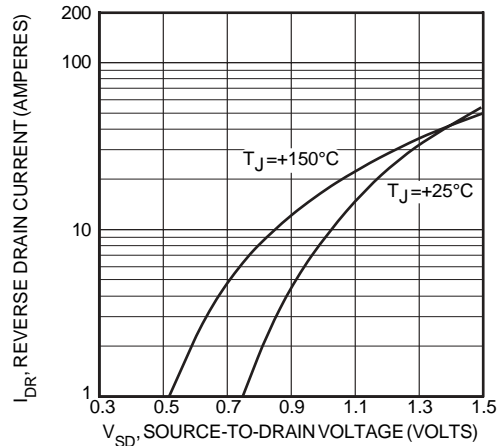
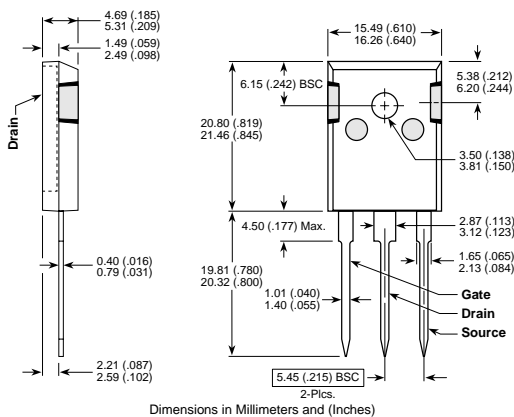


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-247 Package Outline



D<sup>3</sup>PAK Package Outline

